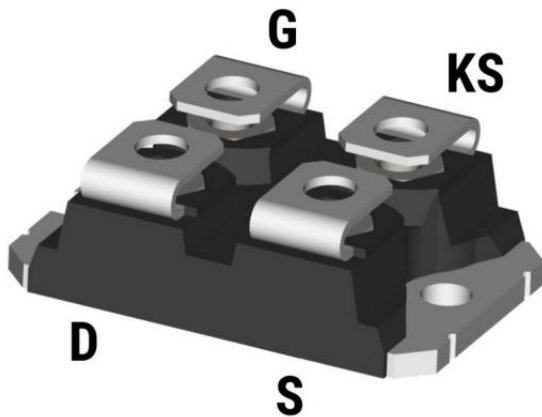


Description

The DFS17SU12Z7C2 is a Single Unit SiC MOSFET Power Module. It integrates high performance SiC MOSFET chips designed for the applications such as Motor drives and EV charging.



Features

- 1200V/17mΩ @ $T_j = 25^{\circ}\text{C}$, $V_{GS} = 18\text{V}$
- 175°C maximum junction temperature
- Low Device Capacitances(C_{oss} , C_{rss})
- AlNAMB substrate
- Faster and More Efficient Switching

Applications

- UPS
- Motor Drive
- EV Charging
- High Voltage DC-DC Converters
- Induction Heating and Welding
- Smart Grid Transmission and Distribution

Circuit diagram

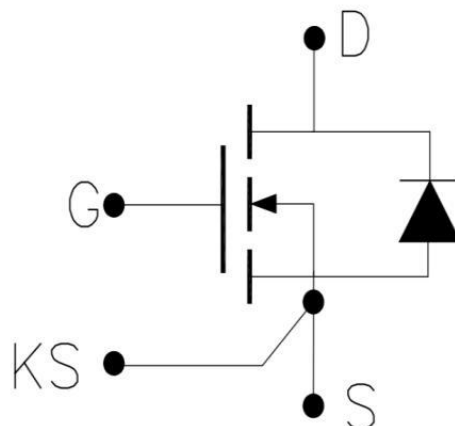


Figure 1. Out drawing & circuit diagram for DFS17SU12Z7C2

Pin Configuration and Marking Information

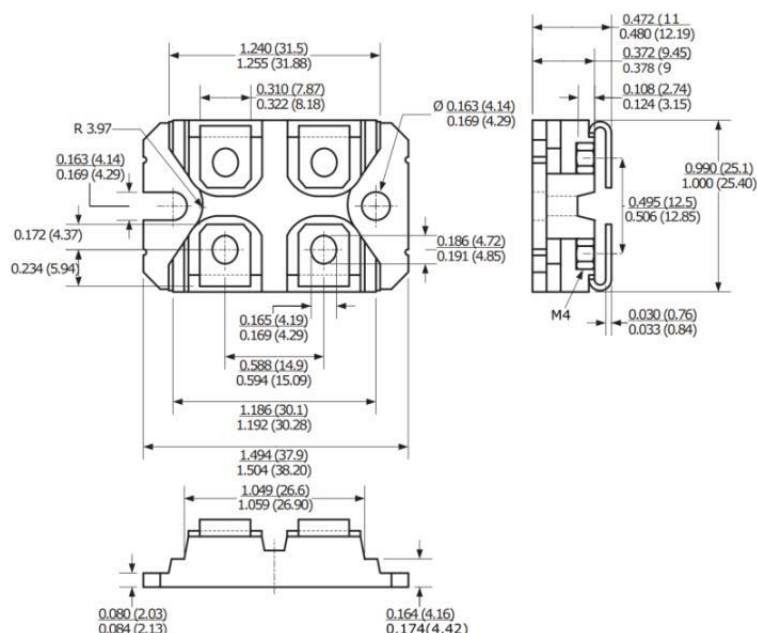


Figure 2. Pin configuration

Module

Parameter	Conditions	Value	Unit
Isolation Voltage	RMS, f=50Hz, t=1min	3.4	KV
CTI	-	>400	-
Mounting torque for module mounting	M4	1.5	Nm
Weight	-	28	g

Maximum Ratings (T_j =25°C unless otherwise specified)

Symbol	Parameter	Conditions		Ratings	Unit
V _{DSS}	Drain-Source Voltage	G-S Short		1200	V
V _{GSS}	Gate-Source Voltage	D-S Short, AC frequency ≥1Hz, Note1		-10 to +22	V
I _{DS}	DC Continuous Drain Current	V _{GS} =+15V	T _C =25°C	120	A
I _{DS}	DC Continuous Drain Current		T _C =100°C	85	A

I_{DS}	DC Continuous Drain Current	$V_{GS} = +18V$	$T_C = 25^{\circ}C$	125	A
I_{DS}	DC Continuous Drain Current		$T_C = 100^{\circ}C$	90	A
I_{DSM}	Pulse Drain Current	Pulse width $\leq 3\mu s$, $V_{GS} = +15V$, Note2		330	A
P_{tot}	Total Power Dissipation	$T_C = 25^{\circ}C$		350	W
T_{jmax}	Max Junction Temperature	-		175	$^{\circ}C$
T_{stg}	Storage Temperature	-		-50 to 175	$^{\circ}C$

Note1: Recommended Operating Value, +18V/-5V, +15V/-4V

Note2: Pulse width limited by maximum junction temperature

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MOSFET Electrical characteristics (T_j=25°C unless otherwise specified, chip)

Symbol	Item	Condition		Value			Unit	
				Min.	Typ.	Max		
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =100uA		1200	-	-	V	
I _{DSS}	Zero gate voltage drain Current	V _{DS} =1200V, V _{GS} =0V		-	1	-	μA	
V _{GS(th)}	Gate-source threshold Voltage	I _D =35mA, V _{DS} =V _{GS}	T _j =25°C	1.8	2.7	-	V	
			T _j =175°C	-	2.05	-		
I _{GSS}	Gate-Source Leakage Current	V _{GS} =22V, V _{DS} =0V	T _j =25°C	-	-	100	nA	
R _{DS(on)} (Chip)	Static drain-source On-state resistance	I _D =60A V _{GS} =+15V	T _j =25°C	-	20	-	mΩ	
			T _j =175°C	-	29	-	mΩ	
		I _D =60A V _{GS} =+18V	T _j =25°C	-	17	22.5	mΩ	
			T _j =175°C	-	25	-	mΩ	
V _{DS(on)} (Chip)	Static drain-source On-state Voltage	I _D =60A V _{GS} =+15V	T _j =25°C	-	1.20	-	V	
			T _j =175°C	-	1.74	-	V	
		I _D =60A V _{GS} =+18V	T _j =25°C	-	1.02	1.35	V	
			T _j =175°C	-	1.50	-	V	
C _{iss}	Input Capacitance	V _D =800V, V _{GS} =0V, f=1MHz, V _{AC} =25mV		-	5814	-	pF	
C _{oss}	Output Capacitance			-	177	-	pF	
C _{rss}	Reverse transfer Capacitance			-	14.2	-	pF	
Q _g	Total gate charge	V _{DD} =800V, I _D =60A, V _{GS} =+15/-5V		-	180	-	nC	
R _{Gint}	Internal Gate Resistance	T _j =25°C		-	1.3	-	Ω	
t _{d(on)}	Turn-on delay time	V _{DD} =800V I _D =60A V _{GS} =+15/-4V R _{gon} =R _{goff} =1.0Ω	T _j =25°C	-	45	-	ns	
			T _j =150°C	-	39	-		
t _r	Rise time		T _j =25°C	-	18	-	ns	
			T _j =150°C	-	16	-		
t _{d(off)}	Turn-off delay time		I _D =60A V _{GS} =+15/-4V R _{gon} =R _{goff} =1.0Ω	T _j =25°C	-	20	-	ns
				T _j =150°C	-	25	-	
t _f	Fall time			T _j =25°C	-	11	-	ns

		Inductive load switching operation	T _j =150°C	-	35	-	
E _{on}	Turn-on power dissipation		T _j =25°C	-	492	-	μJ
			T _j =150°C	-	662	-	
E _{off}	Turn-off power dissipation		T _j =25°C	-	205	-	μJ
			T _j =150°C	-	200	-	
R _{th(j-c)}	FET Thermal Resistance	Junction to Case		-	0.25	0.35	K/W

Body Diode Electrical characteristics ($T_j=25^\circ\text{C}$ unless otherwise specified, chip)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max	
V _{SD}	Body Diode Forward Voltage	V _{GS} = -5V	T _j = 25°C	-	4.6	-	V
		I _{SD} = 30A	T _j = 175°C	-	4.2	-	
T _{rr}	Reverse recovery time	V _{DD} = 800V, I _D = 60A V _{GS} = +15/-4V	T _j = 25°C	-	35	-	ns
			T _j = 150°C	-	47	-	
Q _{rr}	Reverse recovery charge	R _{gon} = R _{goff} = 1.0Ω Inductive load switching operation	T _j = 25°C	-	240	-	nC
			T _j = 150°C	-	475	-	
I _{rrm}	Reverse recovery current		T _j = 25°C	-	14	-	A
			T _j = 150°C	-	21	-	A

Test Conditions

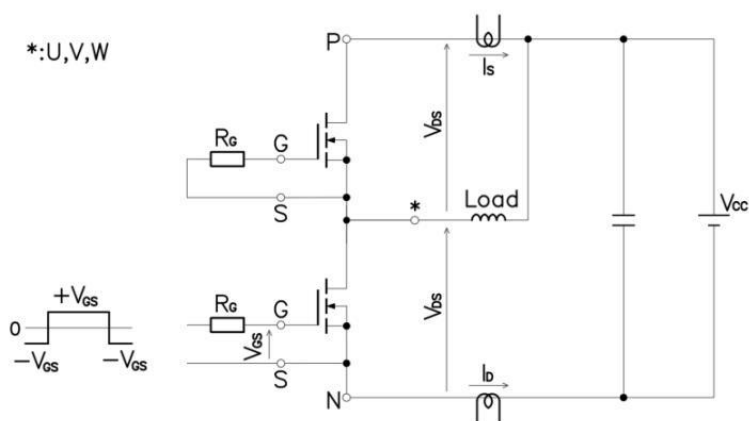


Figure 3. Switching time measure circuit

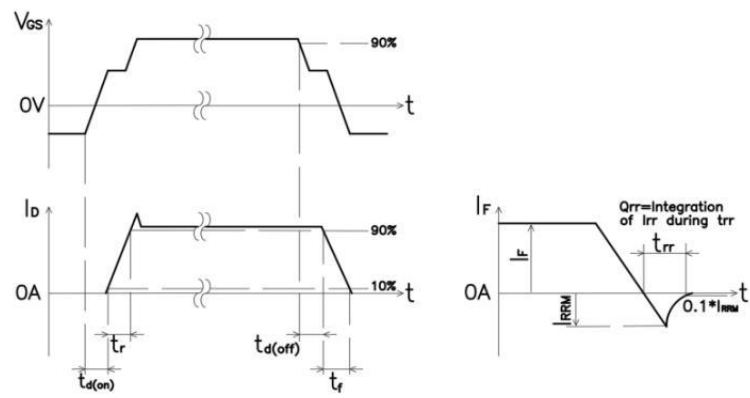


Figure 4. Switching time definition

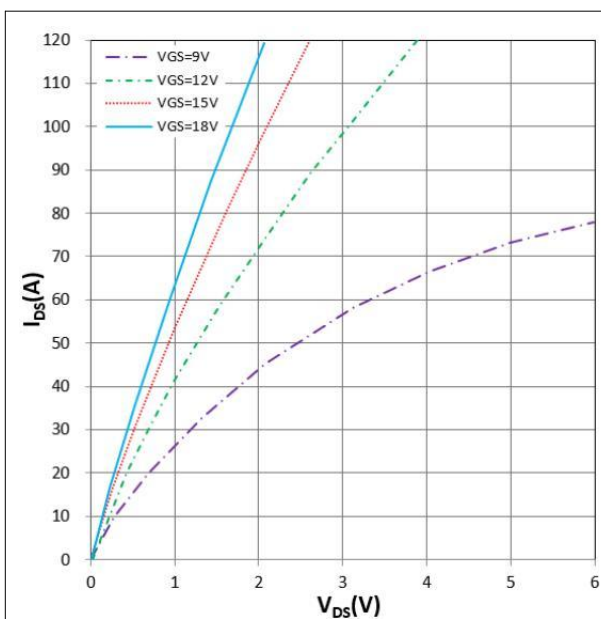


Figure 5. I_{DS} vs V_{DS}
 $T_j = 25^\circ\text{C}$

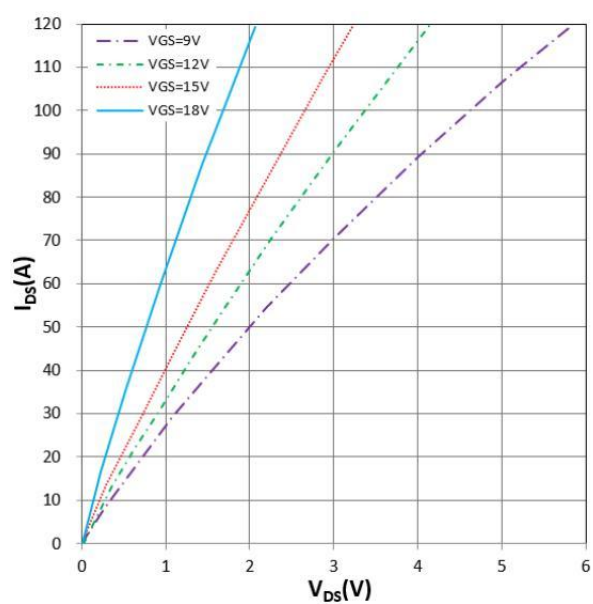


Figure 6. I_{DS} vs V_{DS}
 $T_j = 175^\circ\text{C}$

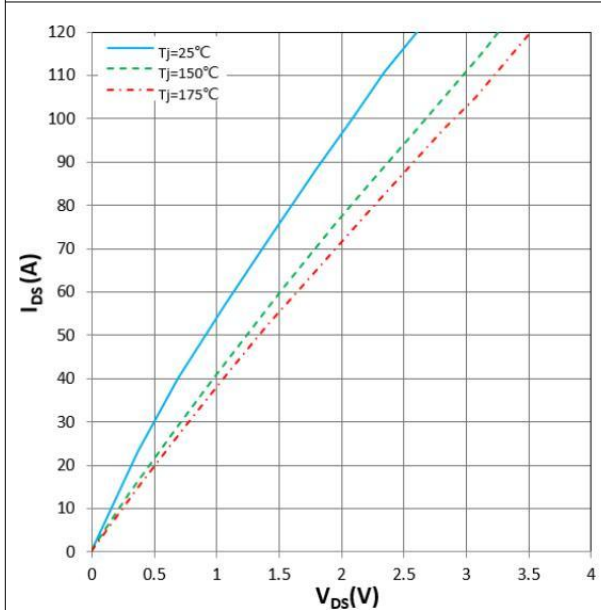


Figure 7. I_{DS} vs V_{DS}
 $V_{GS} = +15\text{V}$

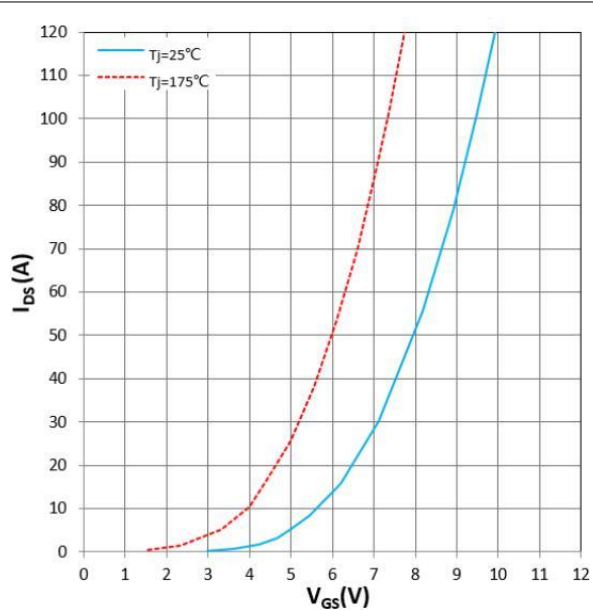


Figure 8. I_{DS} vs V_{GS}
 $V_{DS} = +10\text{V}$

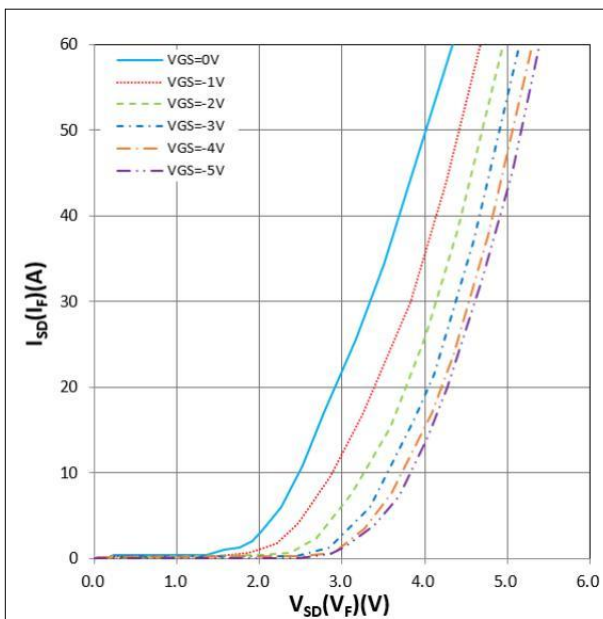


Figure 9. I_{SD} vs V_{SD} (V_F)
 $T_j = 25^\circ\text{C}$

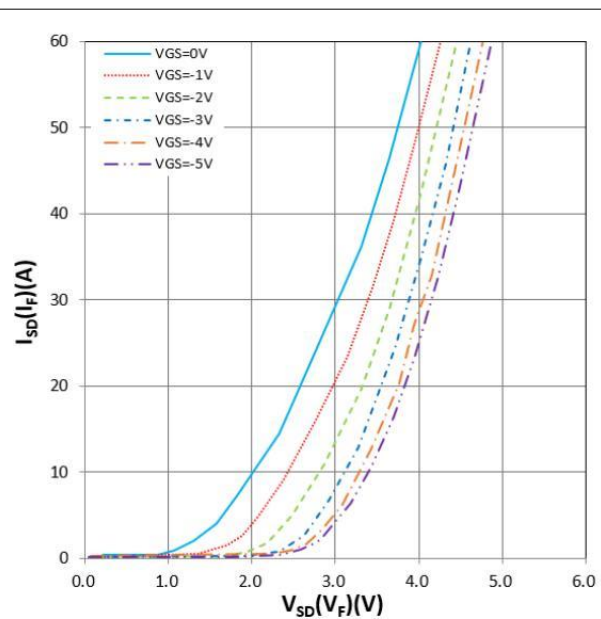


Figure 10. I_{SD} vs V_{SD} (V_F)
 $T_j = 175^\circ\text{C}$

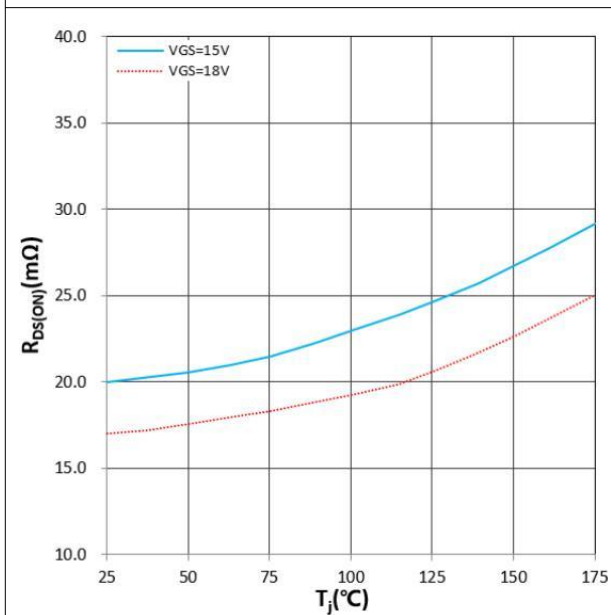


Figure 11. $R_{DS(ON)}$ vs T_j
 $I_D = 60\text{A}$

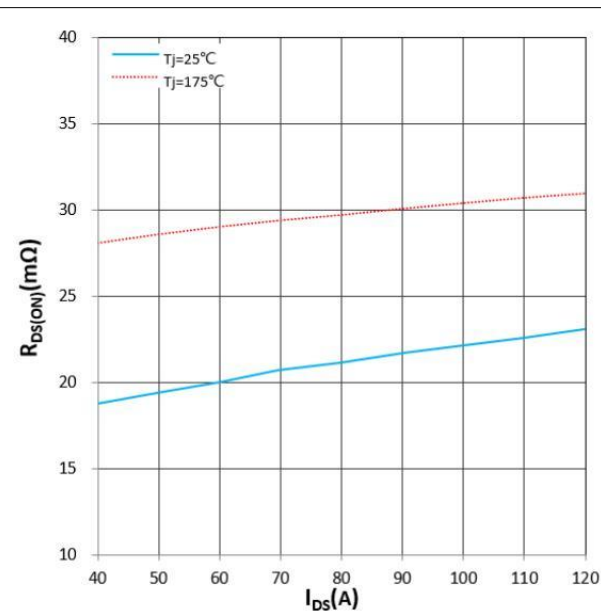


Figure 12. $R_{DS(ON)}$ vs I_{DS}
 $V_{GS} = +15\text{V}$

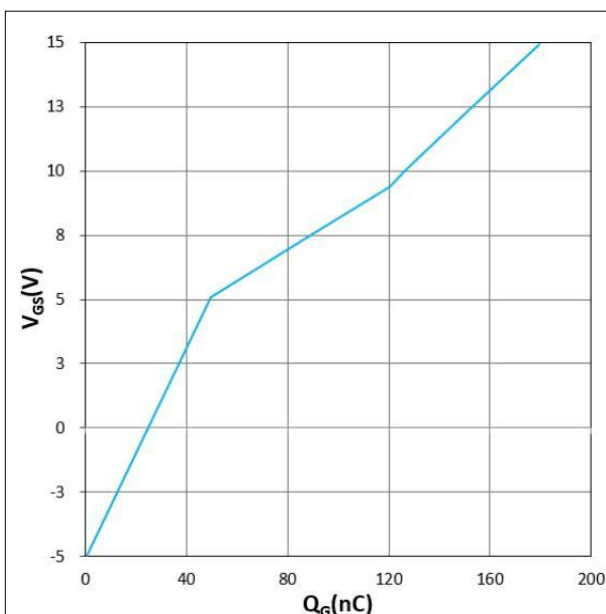


Figure 13. V_{GS} vs Q_g

$V_{DS} = 800V$, $I_D = 60A$, $T_j = 25^\circ C$

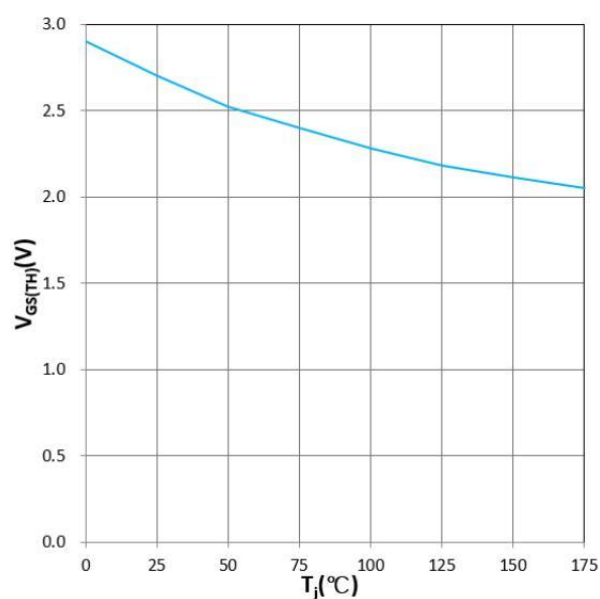


Figure 14. $V_{GS(TH)}$ vs T_j

$V_{GS} = V_{DS}$, $I_D = 35mA$

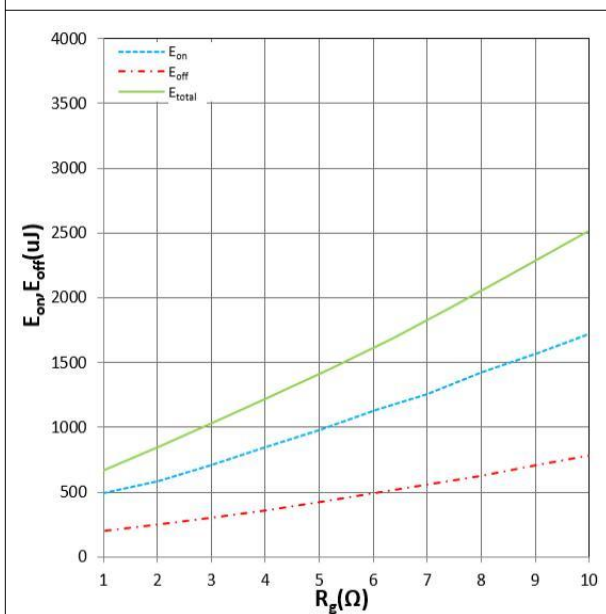


Figure 15. E_{on} , E_{off} vs R_g

$T_j = 25^\circ C$, $V_{CC} = 800V$, $V_{GS} = +15V/-4V$, $I_D = 60A$

Inductive Load

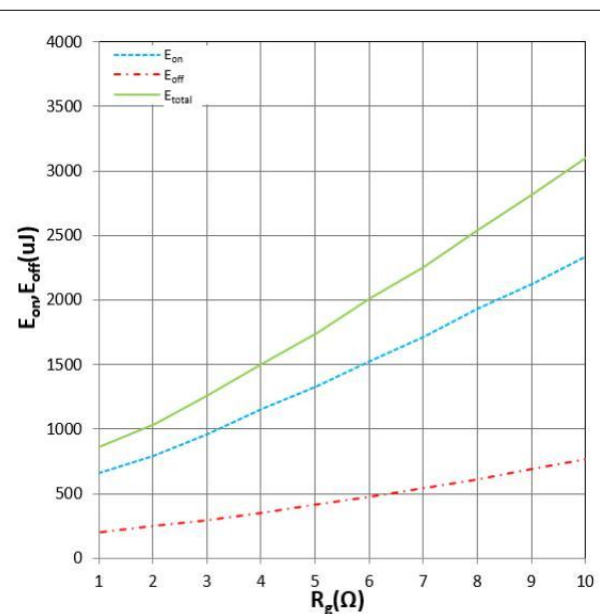


Figure 16. E_{on} , E_{off} vs R_g

$T_j = 150^\circ C$, $V_{CC} = 800V$, $V_{GS} = +15V/-4V$, $I_D = 60A$

Inductive Load

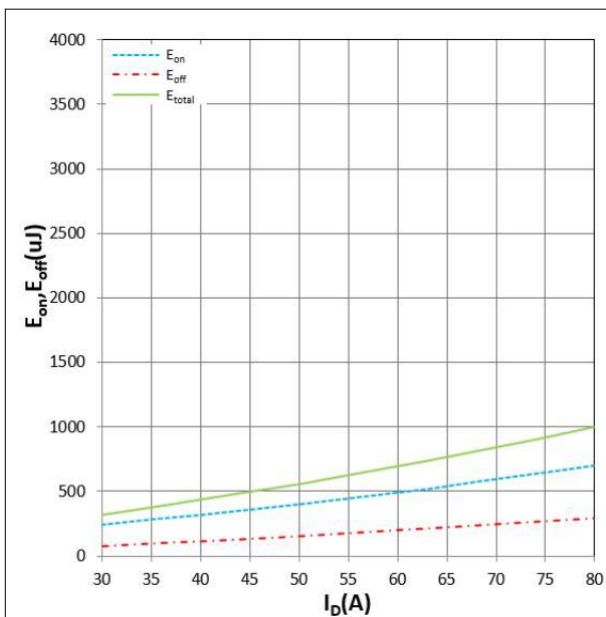


Figure 17. E_{on} , E_{off} vs I_{Ds}

$T_j = 25^\circ\text{C}$, $V_{CC} = 800\text{V}$, $V_{GS} = +15\text{V}/-4\text{V}$

$R_{gon} = R_{goff} = 1.0\Omega$, Inductive Load

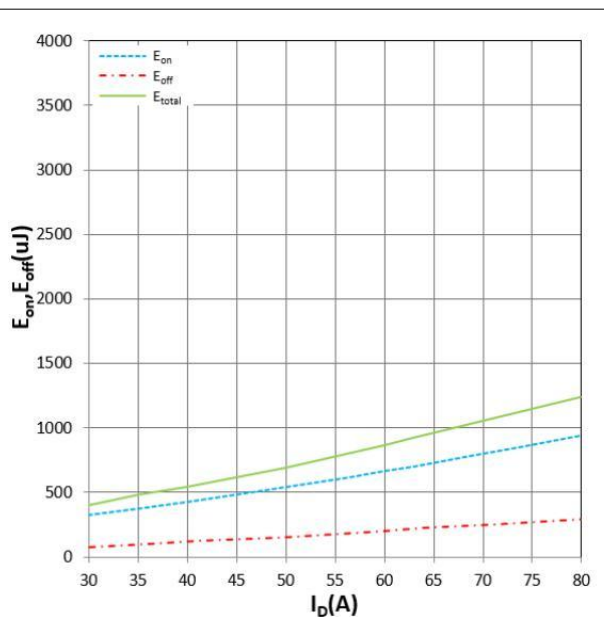


Figure 18. E_{on} , E_{off} vs I_{Ds}

$T_j = 150^\circ\text{C}$, $V_{CC} = 800\text{V}$, $V_{GS} = +15\text{V}/-4\text{V}$

$R_{gon} = R_{goff} = 1.0\Omega$, Inductive Load

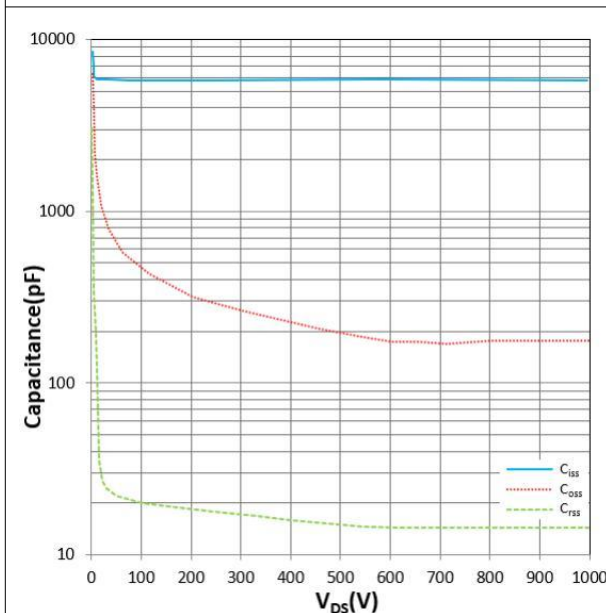


Figure 19. C_{ies} , C_{oss} , C_{rss} vs V_{DS}

$T_j = 25^\circ\text{C}$, $f = 1\text{MHz}$, $V_{AC} = 25\text{mV}$

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